UTRON

UT6264B

Rev 0.9

8K X 8 BIT LOW POWER CMOS SRAM

FEATURES

- Access time : 35/70ns (max.)
- Low power consumption:
  Operating : 60 mA (typical)
  Standby : 3mA (typical) normal
  2 μA (typical) L-version
  1 μA (typical) LL-version
- Single 5V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 28-pin 600 mil PDIP
  28-pin 330 mil SOP

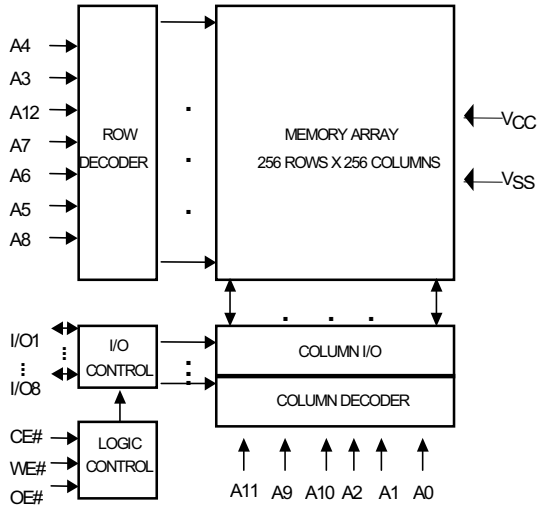
GENERAL DESCRIPTION

The UT6264B is a 65,536-bit low power CMOS static random access memory organized as 8,192 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

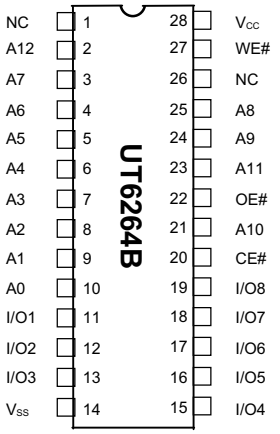
The UT6264B is designed for high-speed and low power application. It is particularly well suited for battery back-up nonvolatile memory application.

The UT6264B operates from a single 5V power supply and all inputs and outputs are fully TTL compatible.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



PDIP/SOP

PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 – A12	Address Inputs
I/O1 – I/O8	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
V_{CC}	Power Supply
V_{SS}	Ground
NC	No Connection

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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}	V_{TERM}	-0.5 to +7.0	V
Operating Temperature	T_A	0 to +70	℃
Storage Temperature	T_{STG}	-65 to +150	℃
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA
Soldering Temperature (under 10 sec)	Tsolder	260	℃

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High - Z	I_{SB}, I_{SB1}
Output Disable	L	H	H	High - Z	I_{CC}
Read	L	L	H	D_{OUT}	I_{CC}
Write	L	X	L	D_{IN}	I_{CC}

Note: H = V_{IH}, L=V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V± 10%, T_A = 0℃ to 70℃)

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Input High Voltage	V_{IH}			2.2	-	V_{CC}+0.5	V
Input Low Voltage	V_{IL}			- 0.5	-	0.8	V
Input Leakage Current	I_{LI}	$V_{SS} \leqq V_{IN} \leqq V_{CC}$		- 1	-	1	μA
Output Leakage Current	I_{LO}	$V_{SS} \leqq V_{I/O} \leqq V_{CC}$ CE#=V_{IH} or OE# = V_{IH} or WE# = V_{IL}		- 1	-	1	μA
Output High Voltage	V_{OH}	I_{OH} = - 1mA		2.4	-	-	V
Output Low Voltage	V_{OL}	I_{OL} = 4mA		-	-	0.4	V
Operating Power Supply Current	I_{CC}	CE# = V_{IL} , $I_{I/O}$ = 0mA Cycle=Min.	- 35	-	60	100	mA
			- 70	-	40	70	mA
Standby Power Supply Current	I_{SB}	CE# = V_{IH} CE#≧V_{CC}-0.2V	Normal	-	1	10	mA
			- L/- LL	-	0.3	3	mA
	I_{SB1}	CE# = V_{IH} CE#≧V_{CC}-0.2V	Normal	-	-	5	mA
			- L		2	100	μA
			- LL	-	1	50	μA

CAPACITANCE (T_A=25℃, f=1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	8	pF
Input/Output Capacitance	$C_{I/O}$	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	C_L = 100pF, I_{OH}/I_{OL} = -1mA/4mA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V± 10% , T_A = 0℃ to 70℃)

(1) READ CYCLE

PARAMETER	SYMBOL	UT6264B-35		UT6264B-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	35	-	70	-	ns
Address Access Time	t_{AA}	-	35	-	70	ns
Chip Enable Access Time	t_{ACE}	-	35	-	70	ns
Output Enable Access Time	t_{OE}	-	25	-	35	ns
Chip Enable to Output in Low Z	t_{CLZ*}	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ*}	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ*}	-	25	-	35	ns
Output Disable to Output in High Z	t_{OHZ*}	-	25	-	35	ns
Output Hold from Address Change	t_{OH}	5	-	5	-	ns

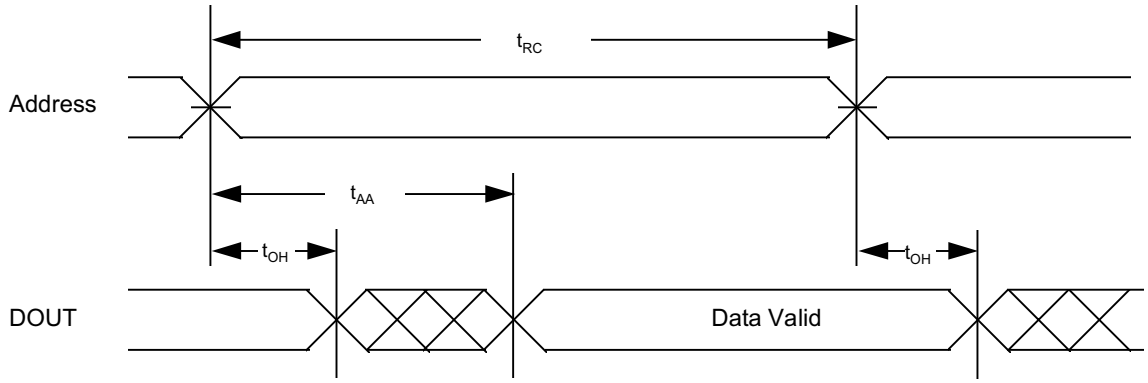
(2) WRITE CYCLE

PARAMETER	SYMBOL	UT6264B-35		UT6264B-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	35	-	70	-	ns
Address Valid to End of Write	t_{AW}	30	-	60	-	ns
Chip Enable to End of Write	t_{CW}	30	-	60	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	ns
Write Pulse Width	t_{WP}	25	-	50	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	20	-	30	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	ns
Output Active from End of Write	t_{OW*}	5	-	5	-	ns
Write to Output in High Z	t_{WHZ*}	-	15	-	25	ns

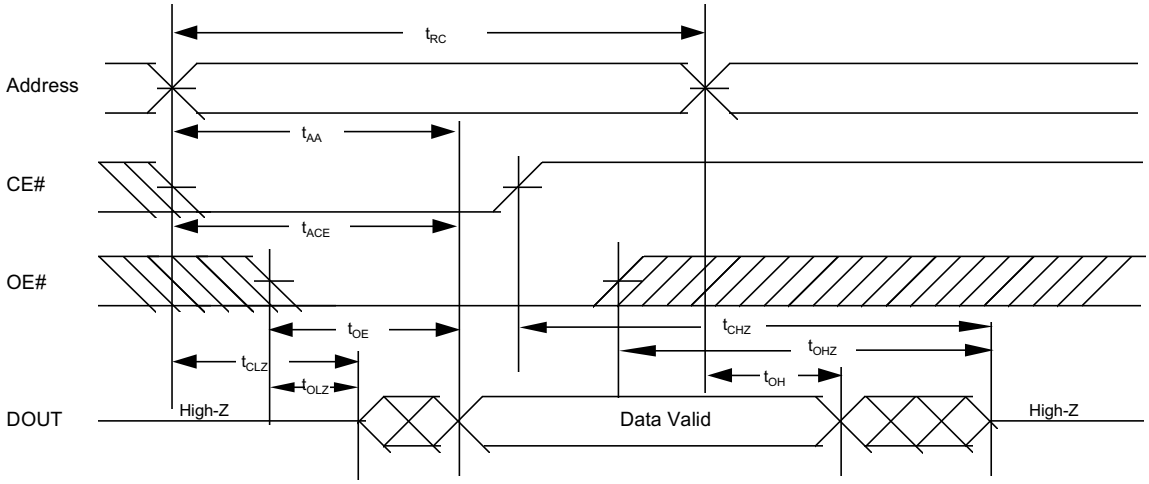
*These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)

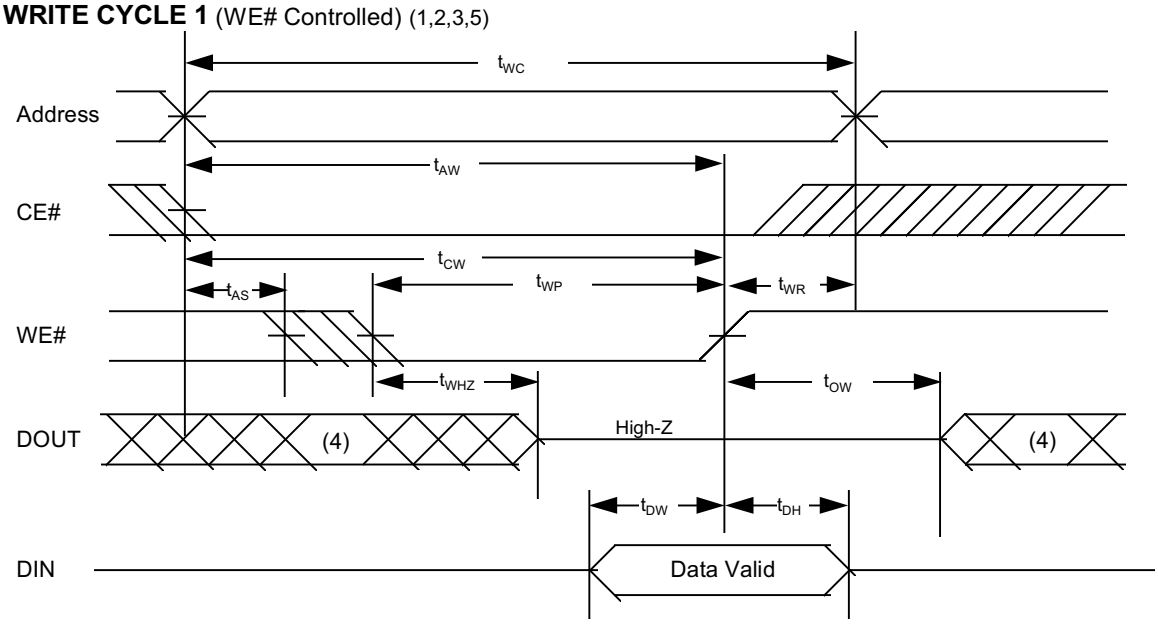


READ CYCLE 2 (CE# and OE# Controlled) (1,3,5,6)

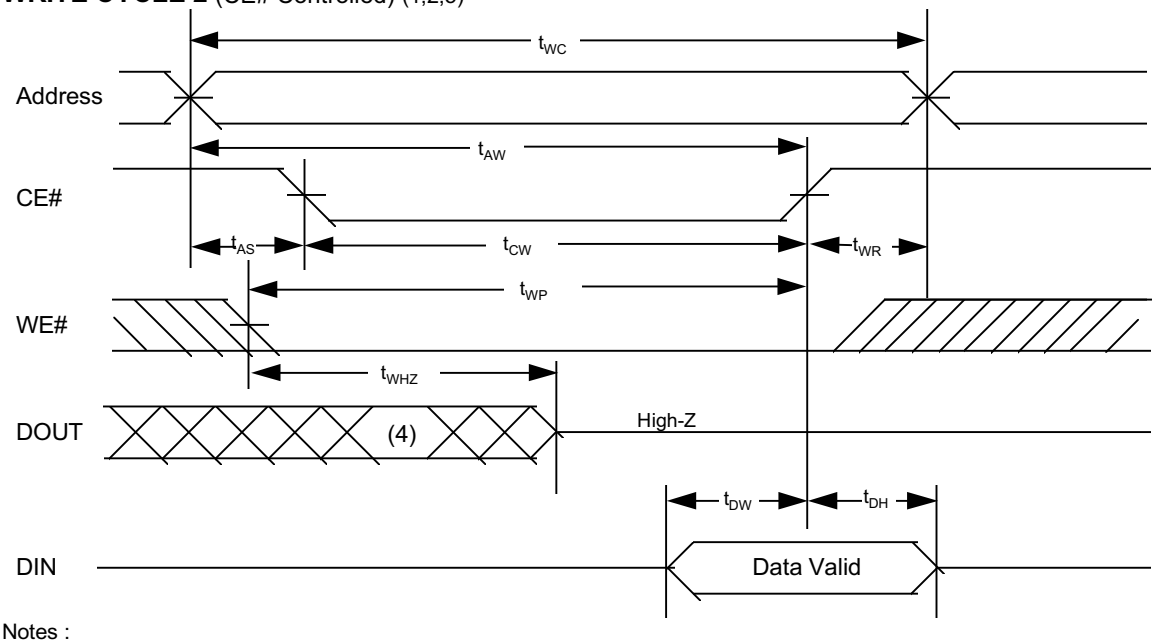


Notes :
1. WE# is HIGH for read cycle.
2. Device is continuously selected CE#=V_{IL}.
3. Address must be valid prior to or coincident with CE# transition; otherwise t_{AA} is the limiting parameter.
4. OE# is LOW.
5. t_{CLZ}, t_{OLZ}, t_{CHZ} and t_{OHZ} are specified with C_L=5pF. Transition is measured ± 500mV from steady state.
6. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ}, t_{OHZ} is less than t_{OLZ}.

WRITE CYCLE 1 (WE# Controlled) (1,2,3,5)



WRITE CYCLE 2 (CE# Controlled) (1,2,5)



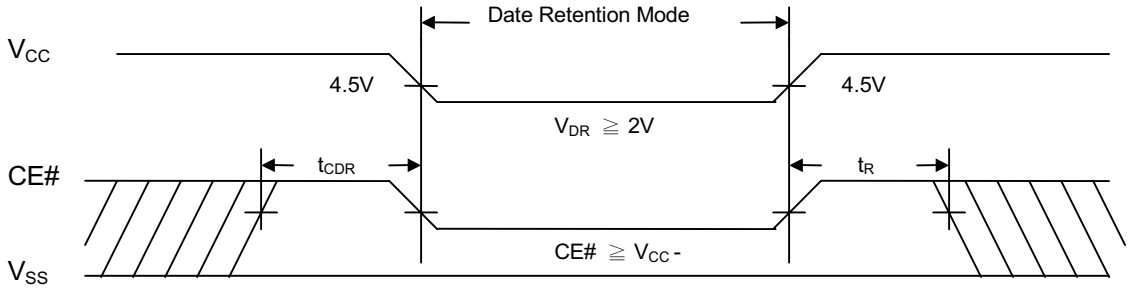
Notes :
1. WE# or CE# must be HIGH during all address transitions.
2. A write occurs during the overlap of a low CE# and a low WE#.
3. During a WE# controlled with write cycle with OE# LOW, t_{WP} must be greater than $t_{WHZ}+t_{DW}$ to allow the I/O drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input singals must not be applied.
5. If the CE# LOW transition occurs simultaneously with or after WE# LOW transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with C_L=5pF. Transition is measured ± 500mV from steady state.

DATA RETENTION CHARACTERISTICS (T_A = 0℃ to 70℃)

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	CE# ≧ V_{CC}-0.2V		2.0	-	5.5	V
Data Retention Current	I_{DR}	Vcc=3V	- L	-	1	50	µA
		CE# ≧ V_{CC}-0.2V	- LL	-	0.5	20	µA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)		0	-	-	ns
Recovery Time	t_R			tRC*	-	-	ns

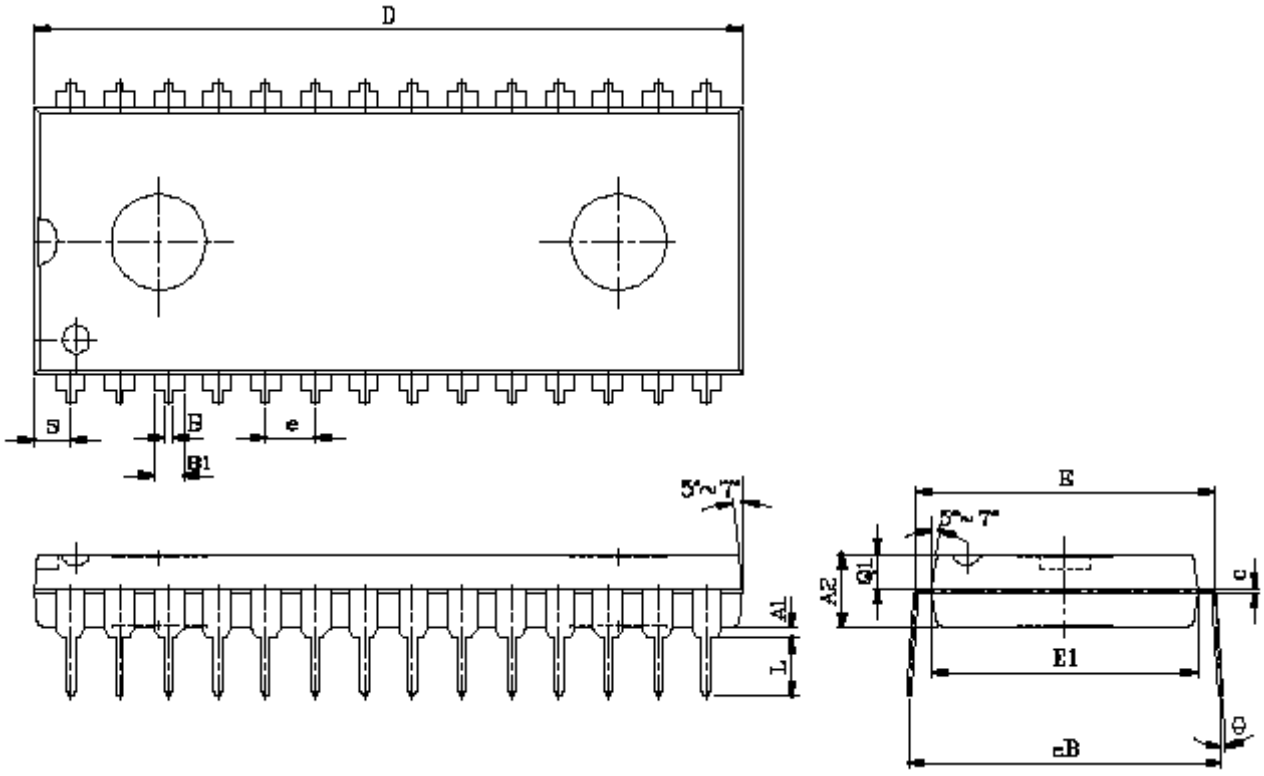
tRC* = Read Cycle Time

DATA RETENTION WAVEFORM



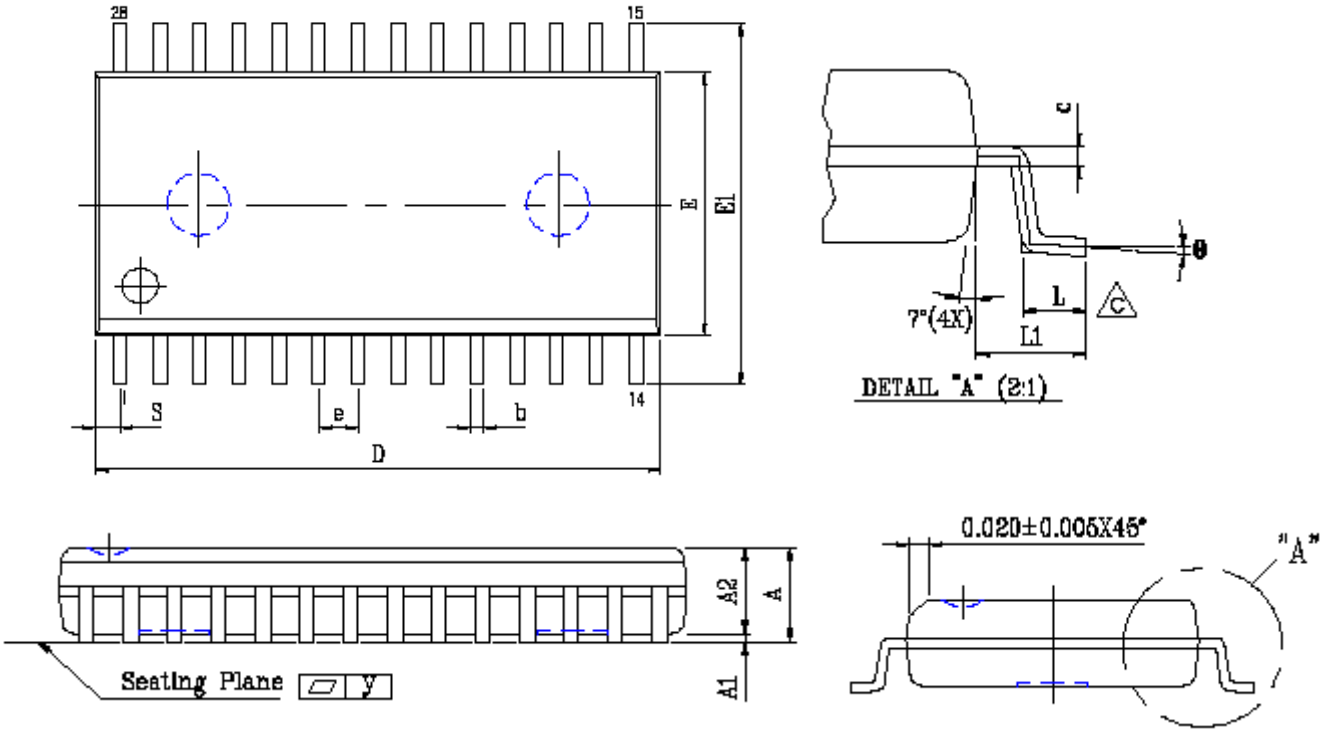
PACKAGE OUTLINE DIMENSION

28 pin 600 mil PDIP Package Outline Dimension



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A1	0.010 (MIN)	0.254 (MIN)
A2	0.150± 0.005	3.810± 0.127
B	0.020 (MAX)	0.508(MAX)
B1	0.055 (MAX)	1.397(MAX)
c	0.012 (MAX)	0.304 (MAX)
D	1.430 (MAX)	36.322 (MAX)
△C E	0.625 (MAX)	15.87 (MAX)
E1	0.52 (MAX)	13.208 (MAX)
e	0.100 (TYP)	2.540(TYP)
eB	0.6 (TYP)	15.24 (TYP)
L	0.180(MAX)	4.572(MAX)
S	0.06 (MAX)	1.524 (MAX)
Q1	0.08(MAX)	2.032(MAX)
Θ	15°(MAX)	15°(MAX)

28 pin 330 mil SOP Package Outline Dimension



SYMBOL \ UNIT	INCH(BASE)	MM(REF)
A	0.120 (MAX)	3.048 (MAX)
A1	0.002(MIN)	0.05(MIN)
A2	0.098± 0.005	2.489± 0.127
b	0.015 (MIN) 0.020 (MAX)	0.38 (MIN) 0.50 (MAX)
c	0.010 (TYP)	0.254(TYP)
D	0.728 (MAX)	18.491 (MAX)
E	0.350 (MAX)	8.890 (MAX)
△B E1	0.465± 0.012	11.811± 0.305
e	0.050 (TYP)	1.270(TYP)
△C L	0.05 (MAX)	1.270 (MAX)
L1	0.067± 0.008	1.702± 0.203
S	0.047 (MAX)	1.194 (MAX)
△E y	0.003(MAX)	0.076(MAX)
θ	0°～10°	0°～10°

ORDERING INFORMATION

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μA)	PACKAGE
UT6264BPC-70	70	5mA	28PIN PDIP
UT6264BPC-70L	70	100 μA	28PIN PDIP
UT6264BPC-70LL	70	50 μA	28PIN PDIP
UT6264BSC-35	35	5mA	28PIN SOP
UT6264BSC-35L	35	100 μA	28PIN SOP
UT6264BSC-35LL	35	50 μA	28PIN SOP
UT6264BSC-70	70	5mA	28PIN SOP
UT6264BSC-70L	70	100 μA	28PIN SOP
UT6264BSC-70LL	70	50 μA	28PIN SOP